

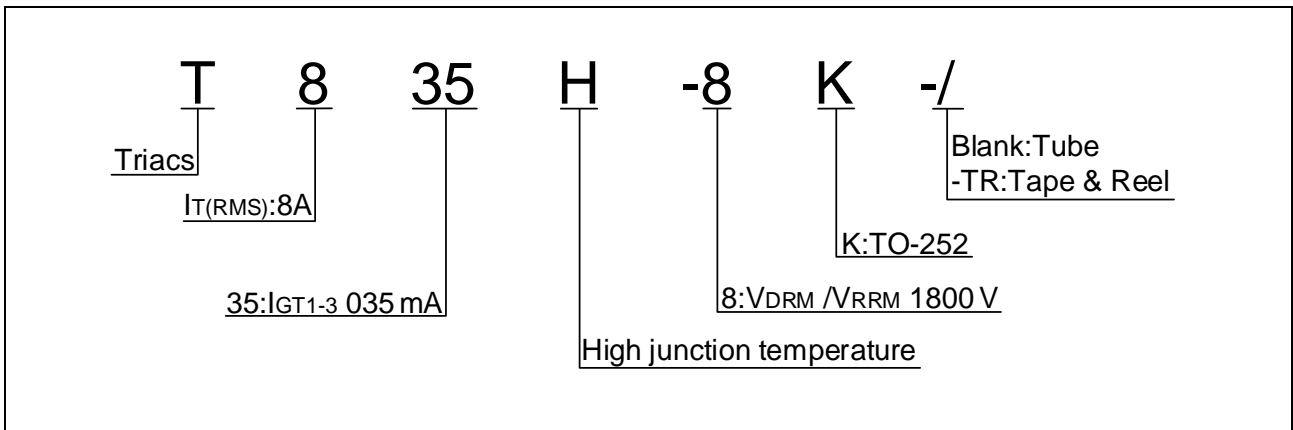
JIEJIE MICROELECTRONICS CO.

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	3	kV
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ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant f, \bar{I}_A, \bar{I}_A	Value	Unit
I_{GT}	$V_D=12V R_L=33$	GBT		

ORDERING INFORMATION



MARKING Year

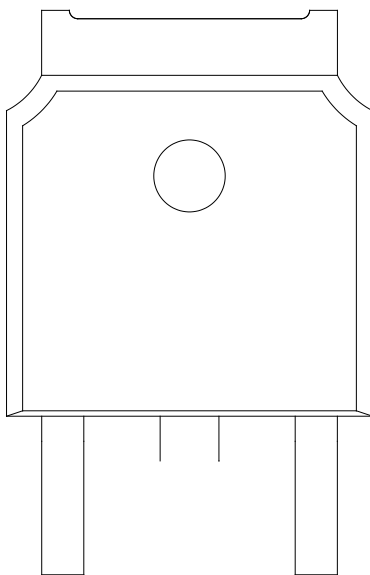


FIG.1: Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

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FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

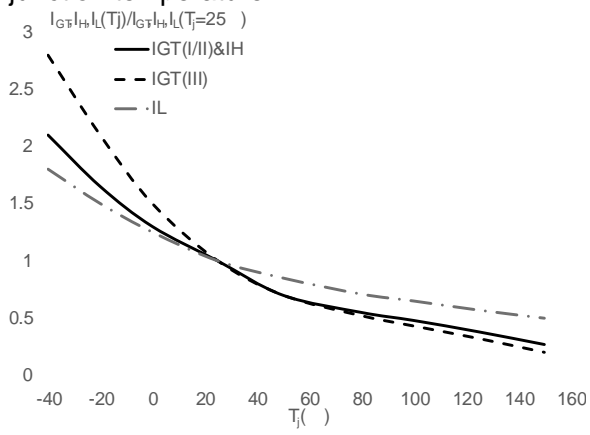
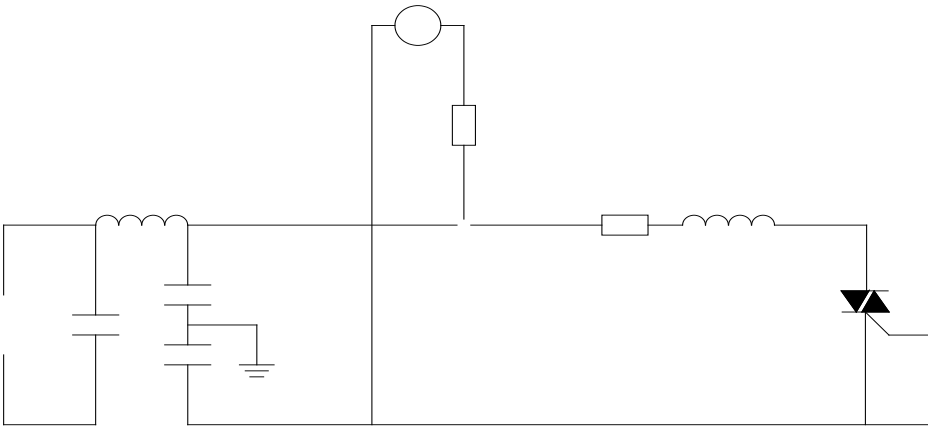


FIG.8 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards



DELIVERY MODE



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